PROCESS CP788X

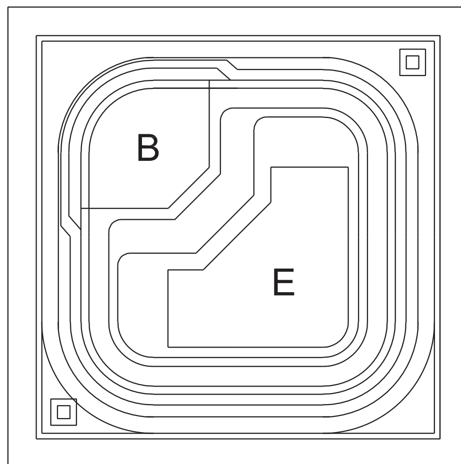
Small Signal Transistor

PNP - Low Noise Amplifier Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	13.7 x 13.7 MILS
Die Thickness	5.9 MILS
Base Bonding Pad Area	4.0 x 4.0 MILS
Emitter Bonding Pad Area	5.5 x 5.5 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

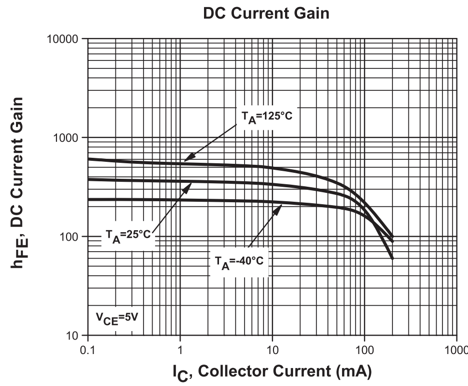
GROSS DIE PER 5 INCH WAFER
91,469

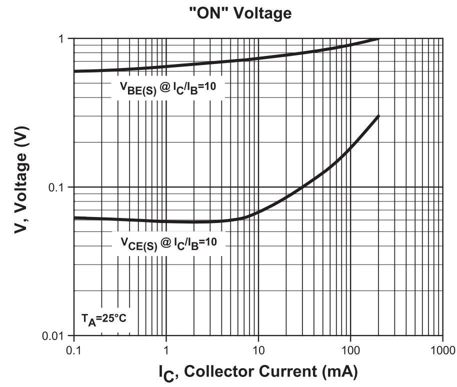
PRINCIPAL DEVICE TYPE
CMKT5087

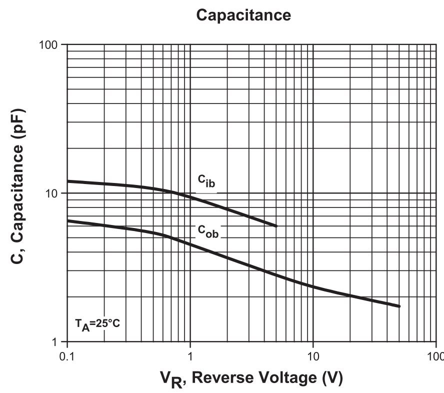
R1 (29-April 2010)

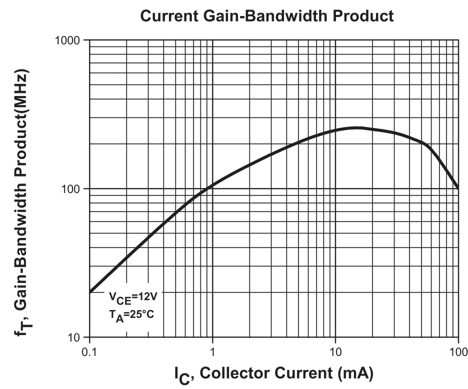
PROCESS CP788X

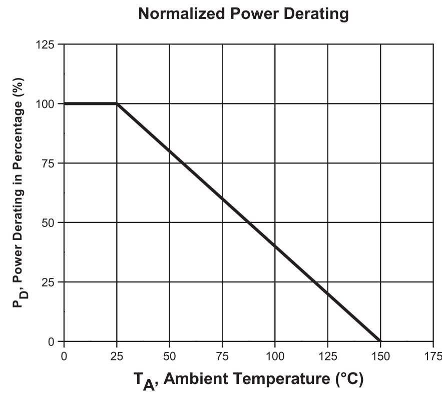
Typical Electrical Characteristics











R1 (29-April 2010)